



Diode type D83 are of modern design with pressure contacts, high alumina ceramic insulator and cold-welding encapsulation. Designed for use in power rectifying circuits and equipment under normal operating conditions.

KEY PARAMETERS

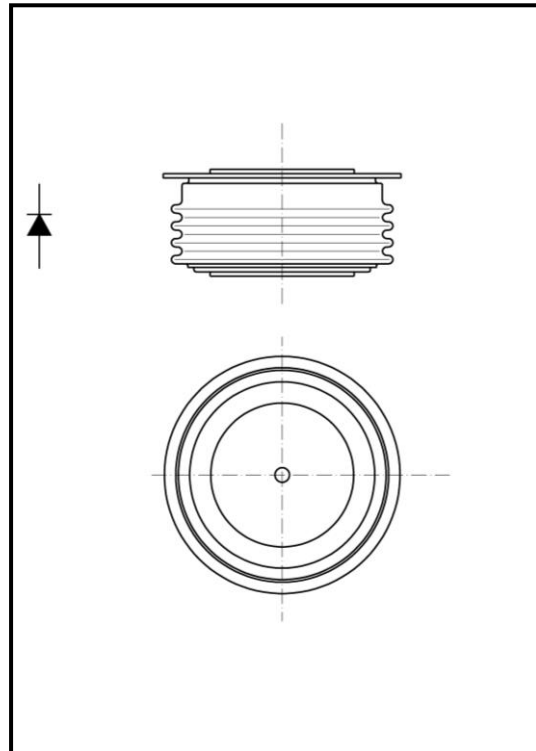
U_{RRM}	up to 4400 V
$I_{F(AV)}$	1000 A
I_{FSM}	11400 A

FEATURES

- all diffused design
- high current capabilities
- high surge current capabilities
- high rated voltages
- low thermal impedance
- tested according to IEC standards
- compact size and small weight

APPLICATION

- High Voltage Power Supplies
- Motor Control
- Battery Chargers
- Free Wheeling Diode
- Resistance Welding



Outline type code: JEDEC DO-200AB
See Package Details for further information

Designed for use in high power industrial and commercial electronic circuits and equipment where high currents are encountered and high reliability is essential. Low forward voltages let minimize energy loss.

ORDERING INFORMATION

When ordering please refer to device code builder presented below.
Please use the complete part number when ordering, quote or in any future correspondence relating to your order.

D83-1000-□□

_____ voltage class (hundreds of volts)

D83-1000

Diode

KKD831000, July 2005 version

ELECTRICAL PARAMETERS

Voltage ratings

Voltage class	U_{RRM}	U_{RSM}	I_{RRM}
	V	V	mA
34	3400	3500	50
36	3600	3700	
38	3800	3900	
40	4000	4100	
42	4200	4300	
44	4400	4500	

Electrical properties

Parameter	Unit	Test conditions	Value
Average forward current @ case temperature	$I_{F(AV)}$	A	1000
	T_c	°C	80
RMS forward current	$I_{F(RMS)}$	A	1570
Surge current	I_{FSM}	A	$T_j=175^\circ\text{C}$, $U_R=0,8U_{RRM}$, $t_p=10\text{ms}$
I^2t – value	I^2t	kA^2s	650
Forward voltage drop max.	U_{FM}	V	$T_j=25^\circ\text{C}$, $I_{FM}=1500\text{A}$
Threshold voltage	$U_{F(T0)}$	V	0,87
Slope resistance	r_F	$\text{m}\Omega$	0,73
Reverse recovery charge	Q_r	μC	$T_j=25^\circ\text{C}$, $I_{FM}=1500\text{A}$, $di_R/dt=25\text{A}/\mu\text{s}$

Thermal properties

Parameter	Unit	Test conditions	Value
Thermal resistance, junction to case	R_{thJC}	°C/W	two sided, DC
Thermal resistance, case to heatsink	R_{thCS}	°C/W	two sided
Operating junction temperature	$T_{jmin} \dots T_{jmax}$	°C	-40...+175
Storage temperature	T_{stg}	°C	-40...+175

Zakłady Elektroniczne LAMINA S.A.
Puławska 34
PL-05-500 Piaseczno
POLAND

Tel.: +48-22-7572731
Tel.: +48-22-3989409
Fax.: +48-22-3989407
e-mail: sekretariat@lamina.com.pl
www.lamina.com.pl

D83-1000

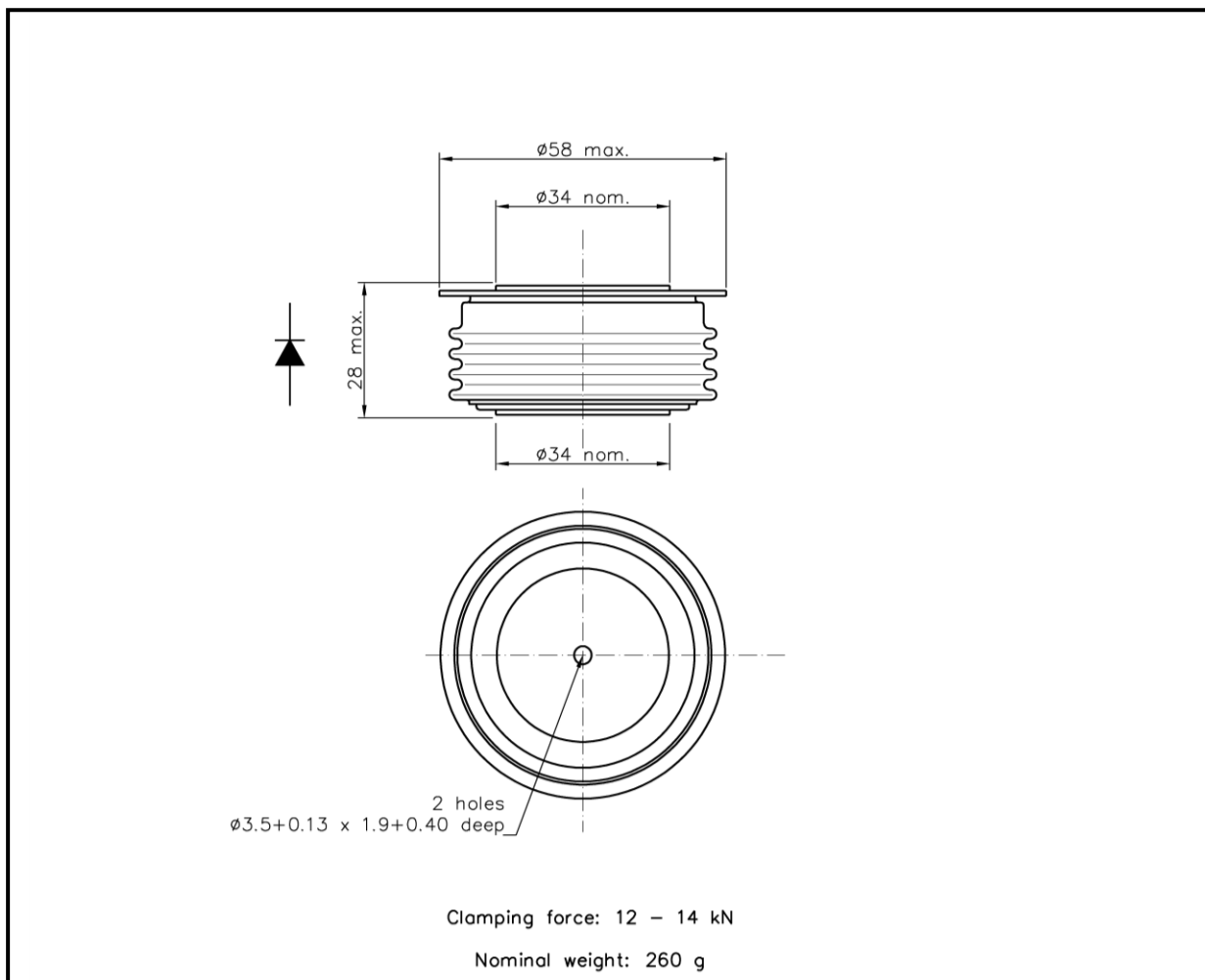
Diode

KKD831000, July 2005 version

Mechanical properties

Parameter		Unit	Value
Clamping force	F_M	kN	12,0 ... 14,0
Weight	m	g	260

Package details



For further package information, please contact Sales & Marketing Department. All dimensions in mm, unless stated otherwise.
Do not scale.

Zakłady Elektronowe LAMINA S.A.
Puławska 34
PL-05-500 Piaseczno
POLAND

Tel.: +48-22-7572731
Tel.: +48-22-3989409
Fax.: +48-22-3989407
e-mail: sekretariat@lamina.com.pl
www.lamina.com.pl

D83-1000

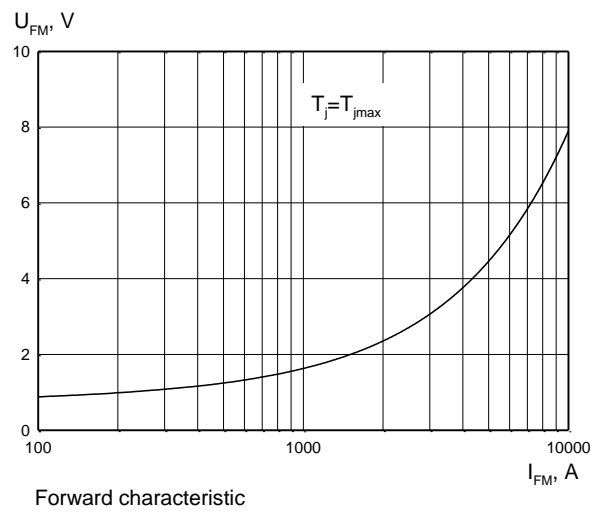
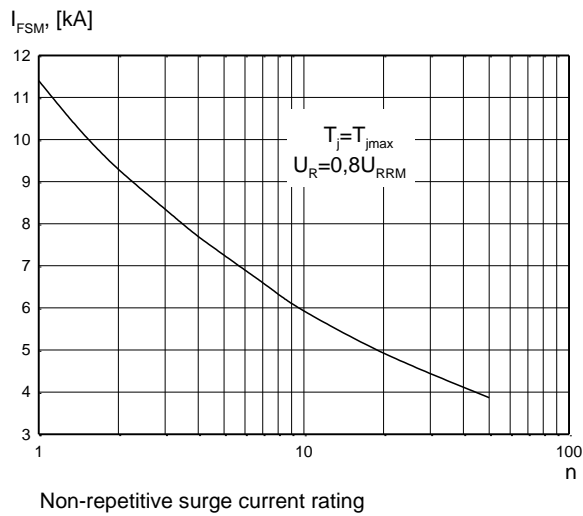
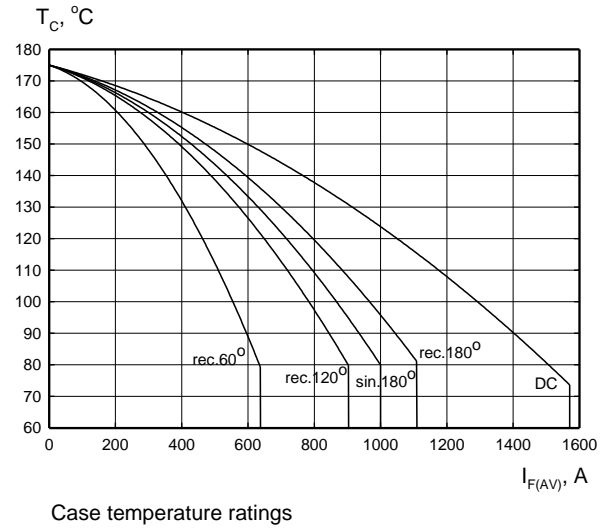
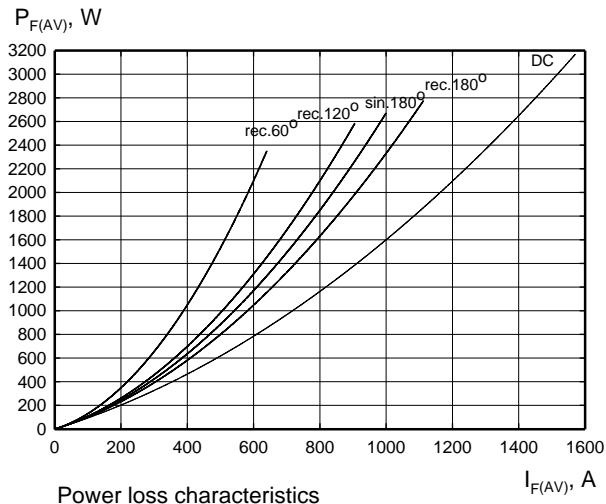
Diode



Zakłady Elektronowe
LAMINA S.A.

KKD831000, July 2005 version

CHARACTERISTICS



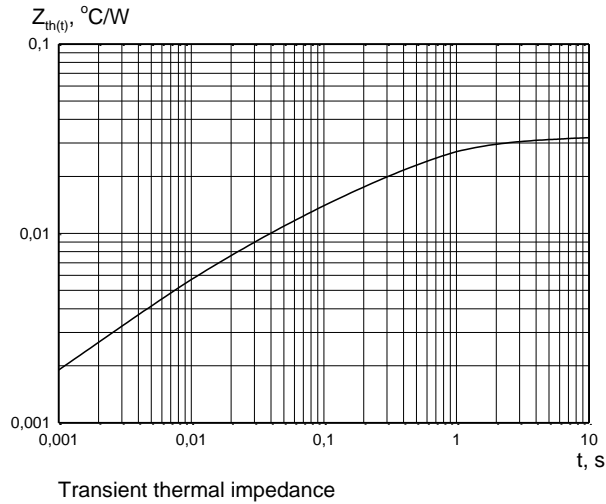
Zakłady Elektronowe LAMINA S.A.
Puławska 34
PL-05-500 Piaseczno
POLAND

Tel.: +48-22-7572731
Tel.: +48-22-3989409
Fax.: +48-22-3989407
e-mail: sekretariat@lamina.com.pl
www.lamina.com.pl

D83-1000

Diode

KKD831000, July 2005 version



HEATSINKS

LAMINA S.I. has its own proprietary range of extruded aluminium heatsinks designed to optimise the performance of our semiconductors with natural and forced air flow. High efficiency water cooled copper heatsinks are also available.

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their best operation. LAMINA S.I. offers a wide selection of clamps to suit all of our manufactured devices.

POWER ASSEMBLY CAPABILITY

LAMINA S.I. provides a support for those customers requiring more than a basic semiconductor and offers precisely assembled Power Blocks according to factory or customer standards.